



安徽富信半导体科技有限公司

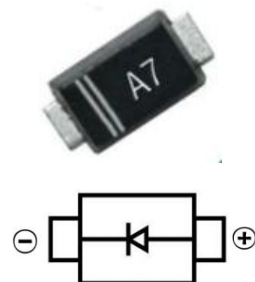
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

A1-A7-SOD123FL

SOD123FL General Purpose Rectifier Diode 通用整流二极管

■ Features 特点

- Low forward voltage drop 低正向压降
- Low reverse leakage current 低反向漏电流
- High surge current capability 高浪涌电流能力
- Surface mount device 表面贴装器件
- Case 封装:SOD123FL



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	A1	A2	A3	A4	A5	A6	A7	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	1							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	25							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	80							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$							

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	V_F		1.0	1.1	V	$I_F=1\text{A}$
Reverse Current($T_A=25^{\circ}\text{C}/$) 反向电流($T_A=100^{\circ}\text{C}/$)	I_R			5 50	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		15		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

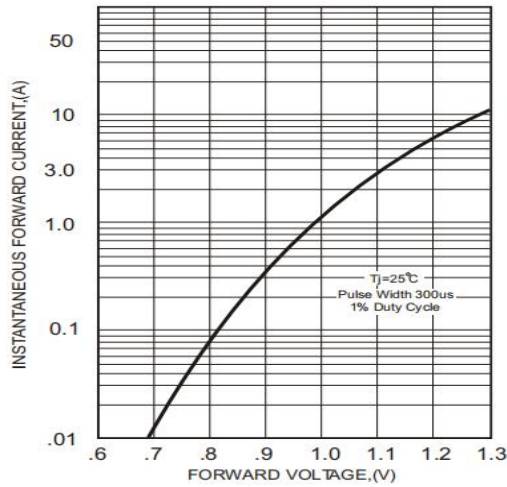


Figure 1: Forward Characteristics

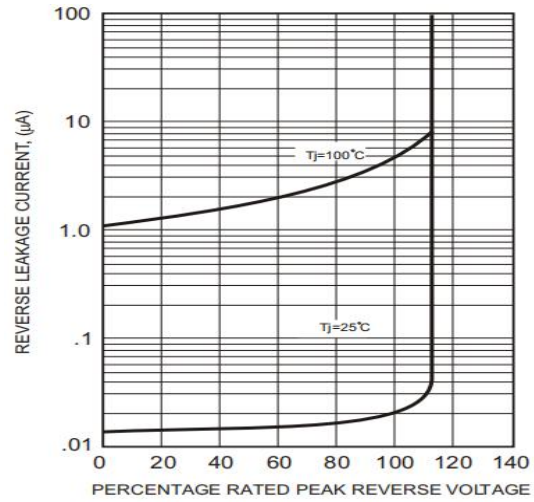


Figure 2: Reverse Characteristics

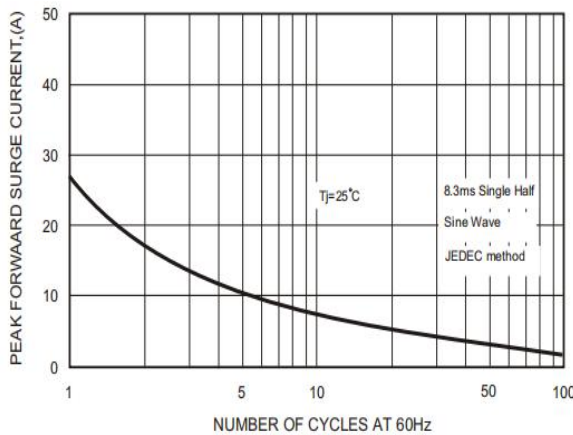


Figure 3: Surge Current Characteristics

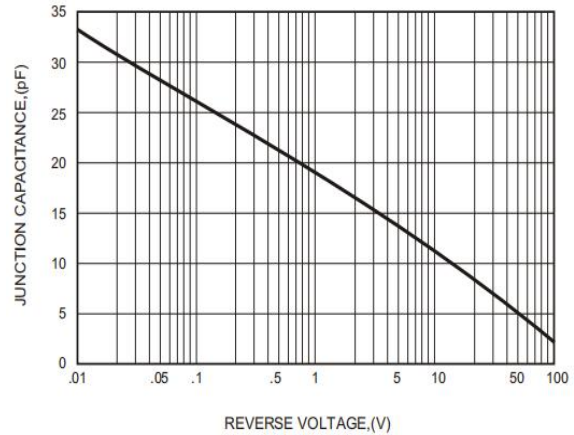


Figure 4: Junction Capacitance

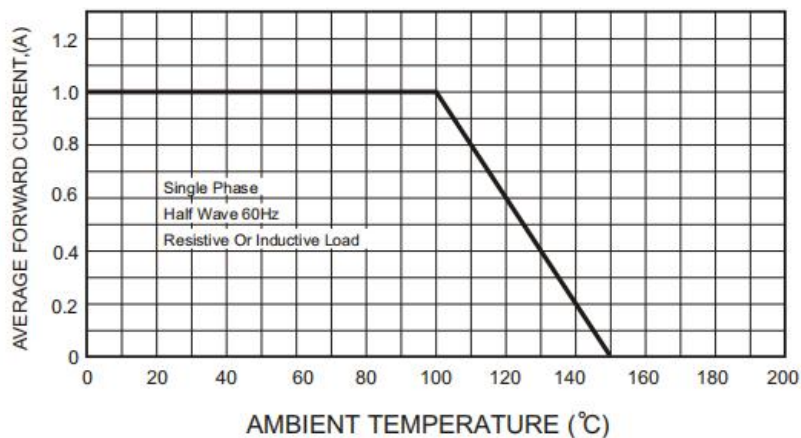
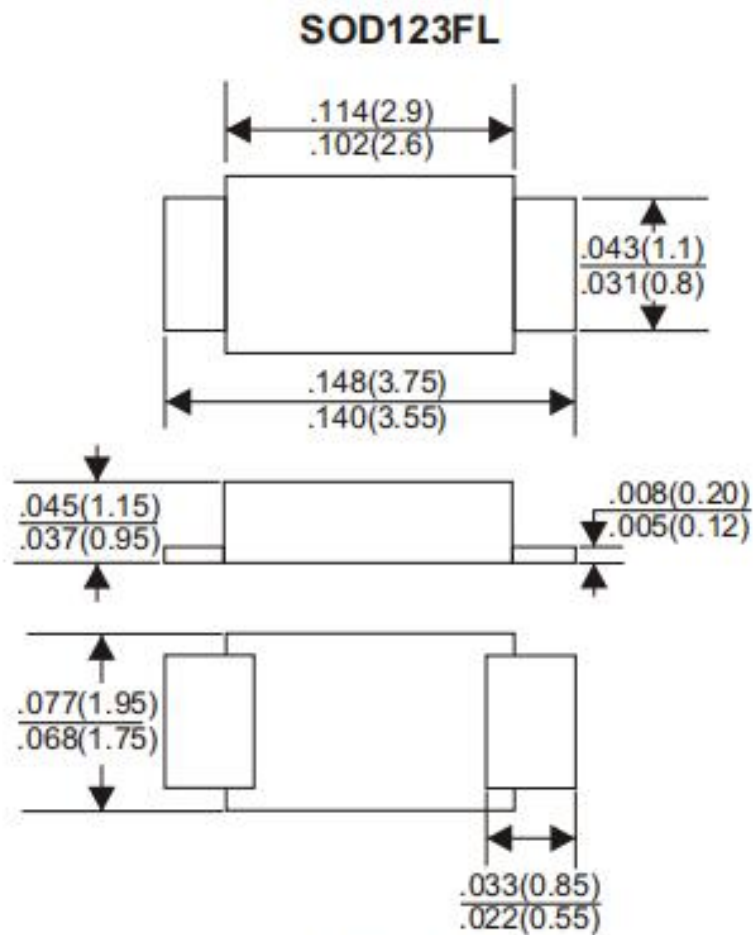


Figure 5: Forward Current Derating

■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)

单击下面可查看定价，库存，交付和生命周期等信息

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